

IN THE CLAIMS:

Cancel claims 31 and 32.

Please amend the claims as follows:

- 1-22. (Previously Canceled)
- 23. (Currently Amended) A pixel, comprising: a single-layered substrate further comprising:
 - a generally planar surface <u>having an upper surface comprising semiconductive material</u>

 <u>having an impurity concentration the greatest at the upper surface of the generally planar surface;</u>[, and]
 - at least one protuberance <u>formed</u> from said generally planar surface; and
 an impurity offset from said generally planar surface and within said protuberance,

 [wherein] said impurity within said protuberance has a concentration <u>decreasing</u>

 [increasing] concurrently with a distance from <u>the upper surface of</u> said generally planar surface.
- 24. (Previously Presented) The pixel in claim 23, wherein said impurity is located within said protuberance to the exclusion of said substrate.
- 25. (Currently Amended) A field emission display, comprising:

 a [an] remaining portion of a single-layered substrate, the remaining portion being an uncontaminated single-layered substrate that is at least semiconductive formed from a single-layered substrate having an upper surface, the single-layered substrate having an impurity concentration greatest at the upper surface while decreasing with a distance from the upper surface; and

- a micro-cathode on said substrate <u>formed from the portion of the single-layered substrate having</u>
 an impurity concentration greatest at the upper surface thereof, further comprising:
 - a contaminated apex <u>having an impurity concentration substantially the same as portion</u>
 of the single-layered substrate at the upper surface thereof;[,] and
 - a decreasingly contaminated body, the concentrate of the impurity decreasing from the contaminated apex.
- 26. (Previously Presented) The field emission display of claim 25, wherein said micro-cathode is integral with said substrate.
 - 27. (Currently Amended) A display panel, comprising:
- a generally uncontaminated substrate <u>comprising semiconductive material formed from a single-layered substrate having an upper surface, the single-layered substrate having an impurity concentration greatest at the upper surface while decreasing with a distance from the upper surface; and</u>
- an emitter electrode on said substrate, further comprising an apex <u>having an impurity</u>

 <u>concentration substantially the same as portion of the single-layered substrate at the upper surface thereof</u>, and further having an etch-resistible quality that increases with depth from said apex.
- 28. (Previously Presented) The display panel in claim 27, wherein said emitter electrode further comprises a base and further has an oxidizable quality that increases with elevation from said base.
- 29. (Previously Presented) The display panel in claim 28, wherein a portion of said substrate that is under said emitter electrode has an etch-resistible quality generally similar to an etch-resistible quality of said base.

- 30. (Previously Presented) The display panel in claim 29, wherein said portion has an oxidizable quality generally similar to an oxidizable quality of said base.
 - 31. (Canceled)
 - 32. (Canceled)